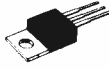


# 2SB511

2SD325供应商



2010A

捷多邦, 专业PCB打样工厂

, 24小时加急出货

PNP/NPN Triple Diffused Planar Silicon Transistor

# 2SD325

## Low Frequency Power Amp Applications

5 Watts AF Power amplifier output use. There are complementary pair.

( ): 2SB511

Absolute Maximum Ratings at Ta=25°C

Collector to Base Voltage	V <sub>CB0</sub>	(-) 35	V
Collector to Emitter Voltage	V <sub>CE0</sub>	(-) 35	V
Emitter to Base Voltage	V <sub>EB0</sub>	(-) 5	V
Collector Current	I <sub>C</sub>	(-) 1.5	A
Peak Collector Current	i <sub>cp</sub>	(-) 3	A
Collector Dissipation	PC	1.75	W
		10	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

Tc=25°C

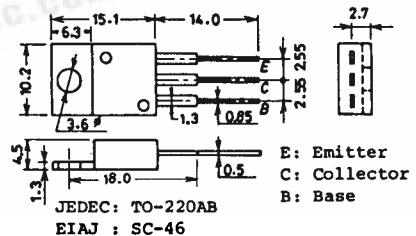
Electrical Characteristics at Ta=25°C

		min	typ	max
Collector Cutoff Current	I <sub>CBO</sub> V <sub>CB</sub> =(-)20V, I <sub>E</sub> =0			(-)0.1
Emitter Cutoff Current	I <sub>EBO</sub> V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0			(-)1.0
DC Current Gain	h <sub>FE</sub> (1) V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)1A	40*		320*
	h <sub>FE</sub> (2) V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)0.1A	35		
Gain Bandwidth Product	f <sub>T</sub> V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)0.5A			8
C-E Saturation Voltage	V <sub>CE(sat)</sub> I <sub>C</sub> =(-)1.5A, I <sub>B</sub> =(-)0.15A			(-)1.0
Base to Emitter Voltage	V <sub>BE</sub> I <sub>C</sub> =(-)1A, V <sub>CE</sub> =(-)5V			(-)1.5

\*: The 2SB511/2SD325 are classified by 1A h<sub>FE</sub> as follows:

40	C	80	60	D	120	100	E	200	160	F	320
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Case Outline 2010A  
(unit:mm)



For details, refer to the description of the 2SD325.

